

MOS FET MTM981400BBF

MTM981400BBF Silicon P-channel MOSFET

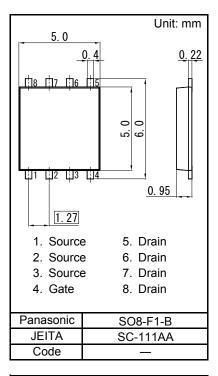
For switching

Features

- Low drain-source On-state Resistance RDS(on) typ = $28 \text{ m}\Omega \text{ (VGS} = -4.5 \text{ V)}$
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol BA

Packaging Embossed type (Thermo-compression sealing) 3 000 pcs / reel (standard)



Internal Connection $(\begin{array}{c} (D) & (D) & (D) \\ 7 & (D) & (D) \\ 6 & (D) \\ 7 & (D) \\ 6 & (D) \\ 1 & (D) \\ 6 & (D) \\ 1 &$

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit			
Drain-source Voltage	VDS	-40	V			
Gate-source Voltage	VGS	±20	V			
Drain Current	ID	-7.0	А			
Drain Current (Pulsed)	IDp	-28	Α			
Total Power dissipation ^{*1}	PD	2	W			
Channel Temperature	Tch	150	°C			
Operating Ambient Temperature	Topr	-40 to +85	°C			
Storage Temperature Range	Tstg	-55 to +150	°C			
Note: *1 Magguring on coramic board at 50 mm × 50 mm × 1.0 mm						

Note: *1 Measuring on ceramic board at 50 mm \times 50 mm \times 1.0 mm.



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■ Electrical Characteristics Ta = 25°C ± 3°C Ctatia Ch.

Static Characteristics						
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-40			V
Zero Gate Voltage Drain Current	IDSS	VDS = -40 V, VGS = 0 V			-10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source threshold Voltage	Vth	ID = -1.0 mA, VDS = -10.0 V	-1		-2.5	V
Drain-source On-state Resistance ^{*1}	RDS(on)1	ID = -7.0 A, VGS = -10 V		19	25	mΩ
	RDS(on)2	ID = -3.5 A, VGS = -4.5 V		28	45	
Forward transfer admittance *1	Yfs	ID = -7.0 A, VDS = -10 V	10			S
Input Capacitance	Ciss			2 700		
Output Capacitance	Coss	VDS = -10 V, VGS = 0 V, f = 1 MH		190		pF
Reverse Transfer Capacitance	Crss	-		175		
Turn-on Delay Time *1,*2	td(on)	VDD = -25 V, VGS = 0 V to -10 V		18		ns
Rise Time ^{*1,*2}	tr	ID = -3.5 A		15		115
Turn-off Delay Time *1,*2	td(off)	VDD = -25 V, VGS = -10 V to 0 V		230		ne
Fall Time *1,*2	tf	ID = -3.5 A		70		ns
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Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

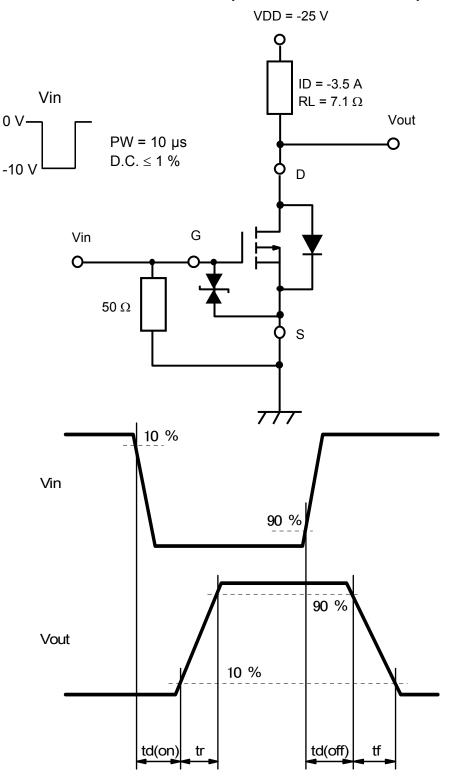
2. *1 Pulse test

*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

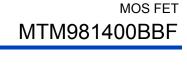
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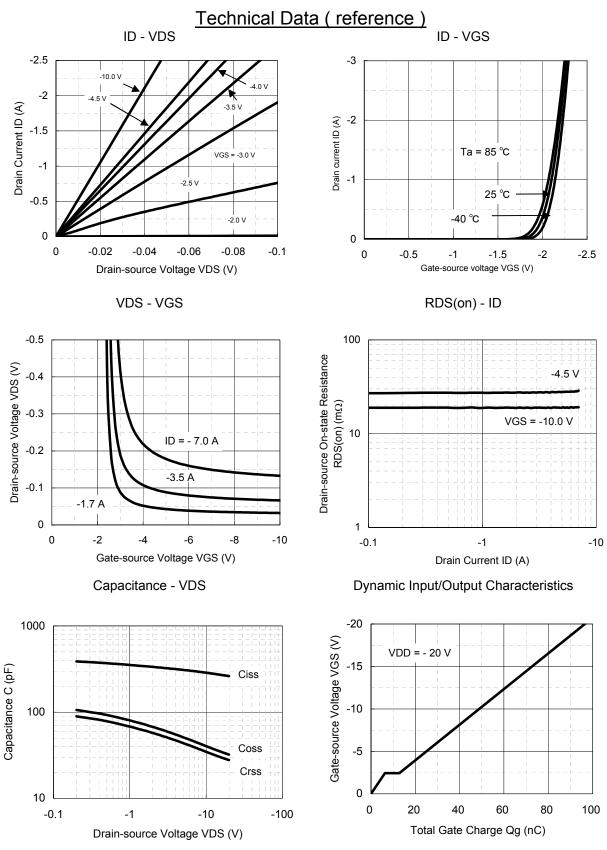


*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



Established : 2007-11-08 Revised : 2013-10-15 **Panasonic**





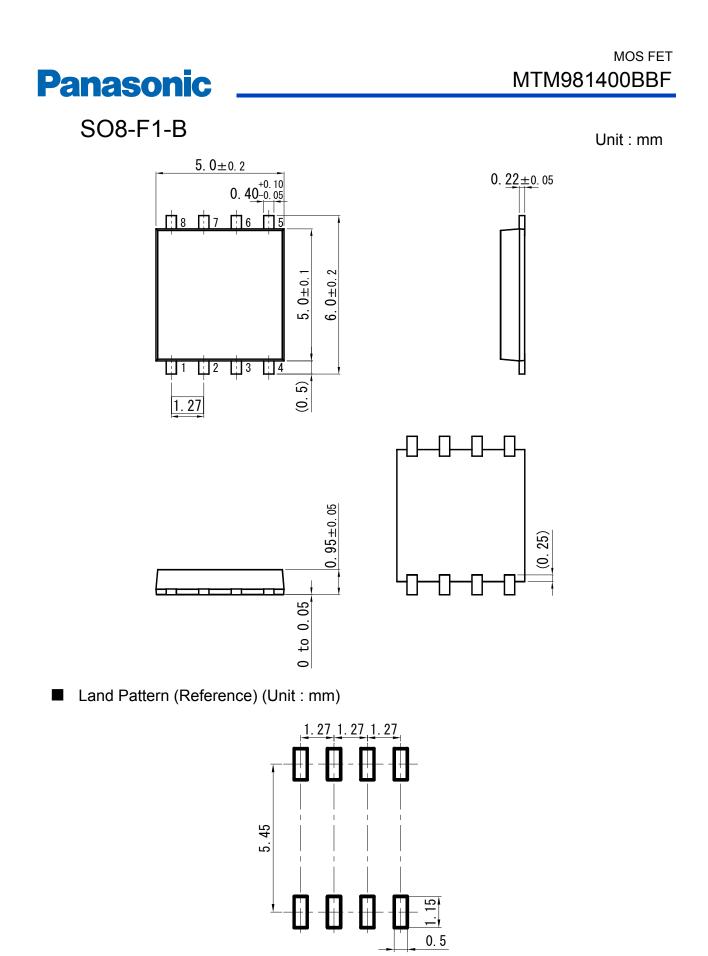
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Established : 2007-11-08 Revised : 2013-10-15

Panasonic MTM981400BBF Technical Data (reference) Vth - Ta -2.5 50 Gate-source Threshold Voltage Drain-source On-resistance -2 40 VGS = -4.5 V RDS(on) (mΩ) 30 -1.5 -10 V Vth (V) 20 -1 10 -0.5 0 0 0 100 -50 50 150 -50 0 50 100 150 Temperature (°C) Temperature (°C) PD - Ta 5 Total Power Dissipation PD (W) 4 Measuring on ceramic board 3 at 50 mm \times 50 mm \times 1.0 mm 2 1 0 0 50 100 150 Temperature Ta (°C) Rth - tsw Safe Operating Area -1000 1000 Thermal Resistance Rth (°C/W) -100 IDp = -28 A Drain Current ID (A) 100 -10 -1 ation in this 10 is limited by RDS(on) 25 °C Glass epoxy board (25.4 \times 25.4 -0.1 coated with copper foil, which has more than 300 mm 1 s DC -0.01 1 1000 -0.01 -1 -10 -100 0.1 1 10 100 -0.1 Drain-source Voltage VDS (V) Pulse Width tsw (s)

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MOS FET



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